

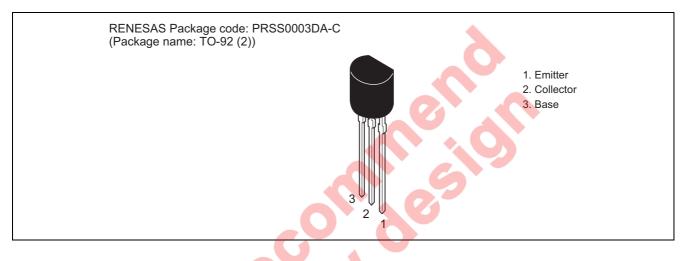
# **2SC535** Silicon NPN Epitaxial Planar

REJ03G0683-0200 (Previous ADE-208-1047) Rev.2.00 Aug.10.2005

## Application

VHF amplifier, mixer, local oscillator

### Outline



## Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Collector to base voltage	V <sub>CBO</sub>	30	V
Collector to emitter voltage	V <sub>CEO</sub>	20	V
Emitter to base voltage	V <sub>EBO</sub>	4	V
Collector current	Ι <sub>C</sub>	20	mA
Collector power dissipation	Pc	100	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

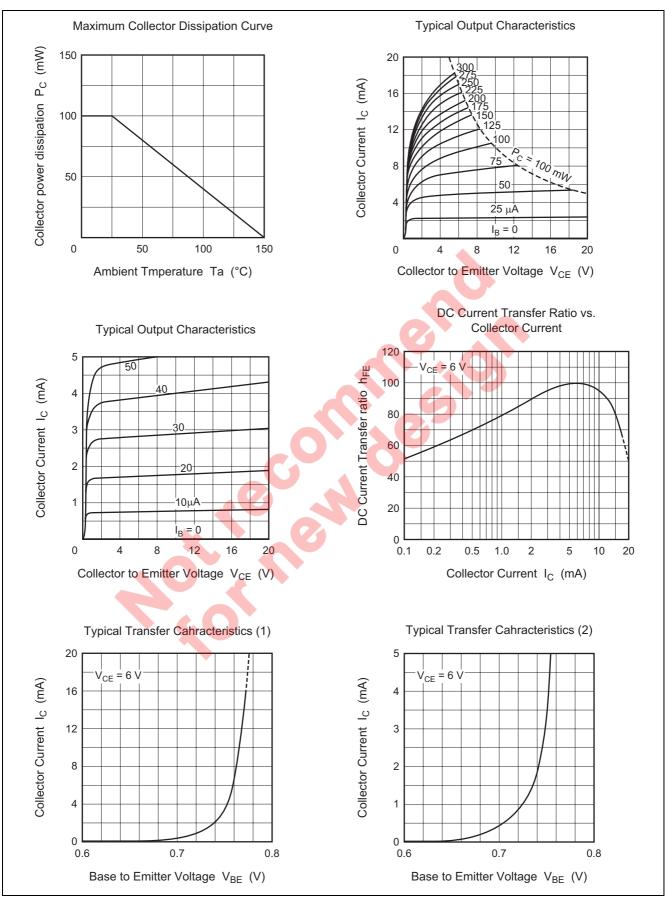


## **Electrical Characteristics**

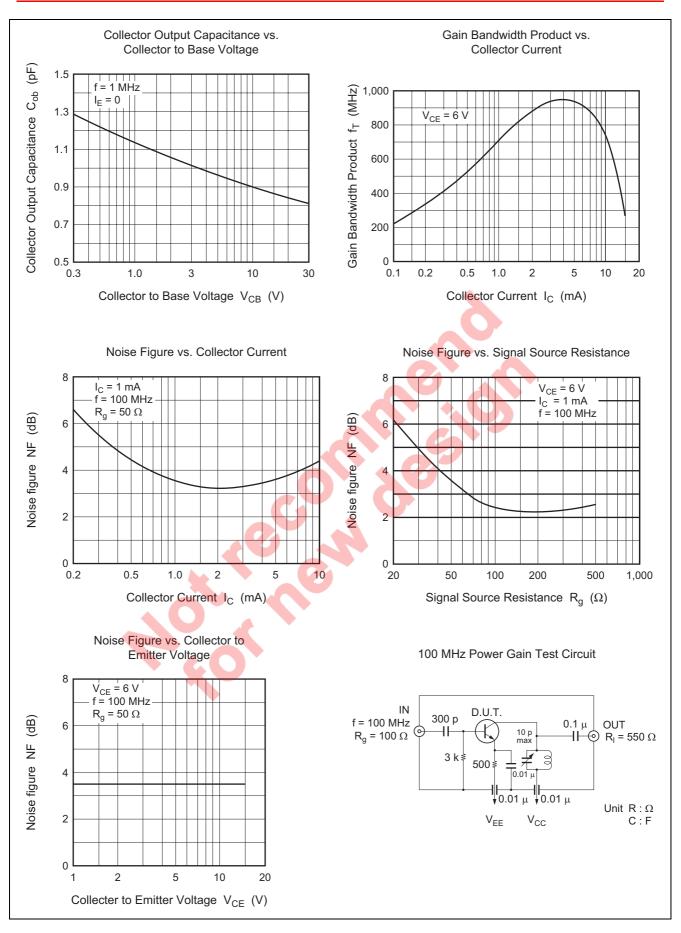
Collector to base breakdown voltage $V_{(BR)CBO}$ 30VI_C = 10 $\mu$ A, I_E =Collector to emitter breakdown voltage $V_{(BR)CEO}$ 20VI_C = 1 mA, R_BEEmitter to base breakdown voltage $V_{(BR)CEO}$ 20VI_C = 1 mA, R_BECollector cutoff currentI_CBOVI_E = 10 $\mu$ A, I_E =Collector cutoff currentI_CBO0.5 $\mu$ A $V_{CB} = 10 V, I_E =$ DC current transfer ratiohFE*160200V_{CE} = 6 V, I_C = 1Base to emitter voltageVBE0.72VV_CE = 6 V, I_C = 1Collector to emitter saturation voltage $V_{CE(sat)}$ 0.17VI_C = 20 mA, I_B =Gain bandwidth productfr450940MHzV_{CE} = 6 V, I_C = 1Collector output capacitanceCob0.91.2pF $V_{CB} = 10 V, I_E =$ Power gainPG1720dB $V_{CE} = 6 V, I_C = 1$ Input admittance (typ)yie1.3 + j5.3mS $V_{CE} = 6 V, I_C = 1$ Reverse transfer admittance (typ)yie0.08 + j0.82mSNote:1. The 2SC535 is grouped by hFE as follows0.08 + j0.82mSNote:1. The 2SC535 is grouped by hFE as follows	= $\infty$ = 0 1 mA 1 mA =4 mA 5 mA = 0, f = 1 MHz 1 mA, 1 mA, g = 50 Ω
Collector to emitter breakdown voltageV(BR)CEO20VIc = 1 mA, RBE :Emitter to base breakdown voltage $V_{(BR)CEO}$ 4VIe = 10 $\mu$ A, Ic =Collector cutoff currentICBO0.5 $\mu$ A $V_{CB} = 10 V$ , Ie =DC current transfer ratiohFE*160200 $V_{CE} = 6 V$ , Ic =Base to emitter voltage $V_{BE}$ 0.72V $V_{CE} = 6 V$ , Ic =Collector to emitter saturation voltage $V_{BE}$ 0.17VIc = 20 mA, IB =Gain bandwidth productfT450940MHz $V_{CE} = 6 V$ , Ic =1CCollector output capacitanceCob0.91.2pF $V_{CE} = 6 V$ , Ic =1CPower gainPG1720dB $V_{CE} = 6 V$ , Ic =1E100 MHzNoise figureNF3.55.5dB $V_{CE} = 6 V$ , Ic =1E100 MHz, RgInput admittance (typ)yie1.3 + j5.3mS $V_{CE} = 6 V$ , Ic =100 MHz, RgNote:1. The 2SC535 is grouped by hFE as follows.mSNote + j0.82mSNote:1. The 2SC535 is grouped by hFE as follows0.08 + j0.82mS	= $\infty$ = 0 1 mA 1 mA =4 mA 5 mA = 0, f = 1 MHz 1 mA, 1 mA, g = 50 Ω
Emitter to base breakdown voltage $V_{(BR)EBO}$ 4VIE = 10 $\mu$ A, Ic =Collector cutoff currentIcBO0.5 $\mu$ AVcB = 10 V, IE =DC current transfer ratiohFE*160200VcE = 6 V, Ic = 10 PA, Ic =Base to emitter voltageVBE0.72VVcE = 6 V, Ic = 10 PA, Ic =Collector to emitter saturation voltageVBE0.72VVcE = 6 V, Ic = 10 PA, Ic	= 0 = 0 1 mA 1 mA = 4 mA 5 mA = 0, f = 1 MHz 1 mA, 1 mA, $g_g = 50$ Ω
Collector cutoff currentIcBO0.5 $\mu$ AVcB = 10 V, IE =DC current transfer ratiohFE*160200VcE = 6 V, Ic = 10 V, IE =Base to emitter voltageVBE0.72VVcE = 6 V, Ic = 10 V, IE =Base to emitter voltageVBE0.72VVcE = 6 V, Ic = 10 V, IE =Collector to emitter saturation voltageVCE(sat)0.17VIc = 20 mA, IB =Gain bandwidth productfT450940MHzVcE = 6 V, Ic = 10 V, IE =Collector output capacitanceCob0.91.2pFVcB = 10 V, IE =Power gainPG1720dBVcE = 6 V, Ic = 10 HzNoise figureNF3.55.5dBVcE = 6 V, Ic = 10 HzInput admittance (typ)yie1.3 + j5.3mSVcE = 6 V, Ic = 10 Hz, Reverse transfer admittance (typ)Yee-0.078 - j0.41mSForward transfer admittance (typ)yie32 - j10mSNote:1. The 2SC535 is grouped by hFE as follows.mSNFE as follows.BC60 to 120100 to 200100 to 200100 to 200	= 0 1 mA 1 mA =4 mA 5 mA = 0, f = 1 MHz 1 mA, 1 mA, $g_{g} = 50 \Omega$
DC current transfer ratio $h_{FE}^{*1}$ 60200 $V_{CE} = 6 \text{ V}, \text{ Ic} = 10 \text{ M}$ Base to emitter voltage $V_{BE}$ $0.72$ $V$ $V_{CE} = 6 \text{ V}, \text{ Ic} = 10 \text{ M}$ Collector to emitter saturation voltage $V_{CE(sat)}$ $0.17$ $V$ $I_C = 20 \text{ mA}, I_B = 10 \text{ M}$ Gain bandwidth product $f_T$ $450$ $940$ MHz $V_{CE} = 6 \text{ V}, \text{ Ic} = 10 \text{ M}$ $I_E = 20 \text{ mA}, I_B = 10 \text{ Collector output capacitance}$ Collector output capacitanceCob $0.9$ $1.2$ $pF$ $V_{CE} = 6 \text{ V}, \text{ Ic} = 10 \text{ MHz}$ Power gainPG $17$ $20$ dB $V_{CE} = 6 \text{ V}, \text{ Ic} = 10 \text{ MHz}$ Noise figureNF $3.5$ $5.5$ dB $V_{CE} = 6 \text{ V}, \text{ Ic} = 100 \text{ MHz}$ Input admittance (typ)yie $1.3 + j5.3$ mS $V_{CE} = 6 \text{ V}, \text{ Ic} = 100 \text{ MHz}$ Forward transfer admittance (typ)yife $32 - j10$ mSOutput admittance (typ)yoe $0.08 + j0.82$ mSNote:1. The 2SC535 is grouped by h_{FE} as follows.mS	1 mA 1 mA =4 mA 5 mA = 0, f = 1 MHz 1 mA, 1 mA, $g_{g} = 50 \Omega$
Base to emitter voltage $V_{BE}$ $0.72$ $V$ $V_{CE} = 6$ $V, I_{C} = 20$ $M, I_{B} = 10$ Collector to emitter saturation voltage $f_T$ 450940MHz $V_{CE} = 6$ $V, I_{C} = 30$ Gain bandwidth product $f_T$ 450940MHz $V_{CE} = 6$ $V, I_{C} = 30$ Collector output capacitanceCob $0.9$ $1.2$ $pF$ $V_{CE} = 6$ $V, I_{E} = 30$ Power gainPG1720dB $V_{CE} = 6$ $V, I_{E} = 30$ Noise figureNF $3.5$ $5.5$ dB $V_{CE} = 6$ $V, I_{E} = 30$ Input admittance (typ)yie $1.3 + j5.3$ mS $V_{CE} = 6$ $V, I_{E} = 30$ Reverse transfer admittance (typ)yfe $32 - j10$ mS $V_{CE} = 6$ $V, I_{E} = 30$ Output admittance (typ)yfe $32 - j10$ mS $MHz$ $V_{CE} = 6$ $V, I_{E} = 30$ Note:1. The 2SC535 is grouped by $h_{FE}$ as follows. $MS$ $MS$ $MS$ $MS$ Mote:1. The 2SC535 is grouped by $h_{FE}$ as follows. $MS$ $MS$ $MS$ $MS$	1 mA =4 mA 5 mA = 0, f = 1 MHz 1 mA, 1 mA, $g_{g} = 50 \Omega$
Collector to emitter saturation voltage $V_{CE(sat)}$ - $0.17$ -V $I_C = 20 \text{ mA}, I_B = 3$ Gain bandwidth product $f_T$ 450940-MHz $V_{CE} = 6 \text{ V}, I_C = 3$ Collector output capacitanceCob- $0.9$ $1.2$ pF $V_{CB} = 10 \text{ V}, I_E = 3$ Power gainPG1720-dB $V_{CE} = 6 \text{ V}, I_C = 3$ Noise figureNF- $3.5$ $5.5$ dB $V_{CE} = 6 \text{ V}, I_C = 3$ Input admittance (typ)yie $1.3 + j5.3$ mS $V_{CE} = 6 \text{ V}, I_C = 3$ Reverse transfer admittance (typ)yfe $32 - j10$ mS $V_{CE} = 6 \text{ V}, I_C = 3$ Output admittance (typ)yfe $32 - j10$ mS $V_{CE} = 6 \text{ V}, I_C = 3$ Note:1. The 2SC535 is grouped by h <sub>FE</sub> as follows.mSmS $MS$	=4 mA 5 mA = 0, f = 1 MHz 1 mA, 1 mA, g <sub>g</sub> = 50 Ω
Gain bandwidth product $f_T$ 450940—MHz $V_{CE} = 6 \text{ V}, I_C = 5$ Collector output capacitanceCob—0.91.2pF $V_{CB} = 10 \text{ V}, I_E = 5$ Power gainPG1720—dB $V_{CE} = 6 \text{ V}, I_C = 5$ Noise figureNF—3.55.5dB $V_{CE} = 6 \text{ V}, I_C = 5$ Input admittance (typ)yie1.3 + j5.3mS $V_{CE} = 6 \text{ V}, I_C = 5$ Reverse transfer admittance (typ)yre $-0.078 - j0.41$ mSOutput admittance (typ)yoe $0.08 + j0.82$ mSNote:1. The 2SC535 is grouped by h <sub>FE</sub> as follows.mSBC60 to 120100 to 200 $100 \text{ to } 200$	5 mA = 0, f = 1 MHz 1 mA, 1 mA, g <sub>g</sub> = 50 Ω
Collector output capacitanceCob0.91.2pF $V_{CB} = 10 \text{ V}, I_E = 10 \text{ PG}$ Power gainPG1720dB $V_{CE} = 6 \text{ V}, I_C = 10 \text{ PG}$ Noise figureNF3.55.5dB $V_{CE} = 6 \text{ V}, I_C = 10 \text{ PG}$ Noise figureNF3.55.5dB $V_{CE} = 6 \text{ V}, I_C = 10 \text{ PG}$ Input admittance (typ)yie1.3 + j5.3mS $V_{CE} = 6 \text{ V}, I_C = 10 \text{ PG}$ Reverse transfer admittance (typ)yie-0.078 - j0.41mSForward transfer admittance (typ)yfe32 - j10mSOutput admittance (typ)yoe0.08 + j0.82mSNote:1. The 2SC535 is grouped by hFE as follows.mSBC60 to 120100 to 200100 to 200	= 0, f = 1 MHz 1 mA, 1 mA, $g_{g} = 50 \Omega$
Power gainPG1720dB $V_{CE} = 6 \text{ V}, \text{ Ic} = 7$ f = 100 MHzNoise figureNF3.55.5dB $V_{CE} = 6 \text{ V}, \text{ Ic} = 7$ f = 100 MHz, RgInput admittance (typ)yie1.3 + j5.3mS $V_{CE} = 6 \text{ V}, \text{ Ic} = 7$ f = 100 MHz, RgReverse transfer admittance (typ)yre-0.078 - j0.41mSForward transfer admittance (typ)yfe32 - j10mSOutput admittance (typ)yoe0.08 + j0.82mSNote:1. The 2SC535 is grouped by hFE as follows.BC60 to 120100 to 200	1 mA, 1 mA, g = 50 Ω
Noise figureNF- $3.5$ $5.5$ dB $V_{CE} = 6$ V, $I_C = 7$ Input admittance (typ)yie $1.3 + j5.3$ mS $V_{CE} = 6$ V, $I_C = 7$ Reverse transfer admittance (typ)yre $-0.078 - j0.41$ mSForward transfer admittance (typ)yfe $32 - j10$ mSOutput admittance (typ)yoe $0.08 + j0.82$ mSNote:1. The 2SC535 is grouped by h <sub>FE</sub> as follows. $mS$	1 mA, g = 50 Ω
Input admittance (typ)yie $1.3 + j5.3$ mS $V_{CE} = 6 V, I_C = 100 \text{ MHz}, R_s$ Reverse transfer admittance (typ)yre $-0.078 - j0.41$ mSForward transfer admittance (typ)yfe $32 - j10$ mSOutput admittance (typ)yoe $0.08 + j0.82$ mSNote:1. The 2SC535 is grouped by hFE as follows.BC60 to 120100 to 200	<sub>g</sub> = 50 Ω
Input admittance (typ)yie $1.3 + j5.3$ mS $V_{CE} = 6 \text{ V}, I_C = 7$ Reverse transfer admittance (typ)yre $-0.078 - j0.41$ mSForward transfer admittance (typ)yfe $32 - j10$ mSOutput admittance (typ)yoe $0.08 + j0.82$ mSNote:1. The 2SC535 is grouped by h <sub>FE</sub> as follows.BC60 to 120100 to 200	-
Reverse transfer admittance (typ)yre $-0.078 - j0.41$ mSForward transfer admittance (typ)yfe $32 - j10$ mSOutput admittance (typ)yoe $0.08 + j0.82$ mSNote:1. The 2SC535 is grouped by hFE as follows.BC60 to 120100 to 200	1 mA,
Reverse transfer admittance (typ)       yre       -0.078 - j0.41       mS         Forward transfer admittance (typ)       yfe       32 - j10       mS         Output admittance (typ)       yoe       0.08 + j0.82       mS         Note:       1. The 2SC535 is grouped by h <sub>FE</sub> as follows.         B       C         60 to 120       100 to 200	,
Forward transfer admittance (typ)       yfe       32 - j10       mS         Output admittance (typ)       yoe       0.08 + j0.82       mS         Note:       1. The 2SC535 is grouped by h <sub>FE</sub> as follows.         B       C         60 to 120       100 to 200	
Output admittance (typ)         yoe         0.08 + j0.82         mS           Note:         1. The 2SC535 is grouped by hFE as follows.           B         C           60 to 120         100 to 200	
Note: 1. The 2SC535 is grouped by $h_{FE}$ as follows. <b>B C</b> 60 to 120 100 to 200	
B C 60 to 120 100 to 200	

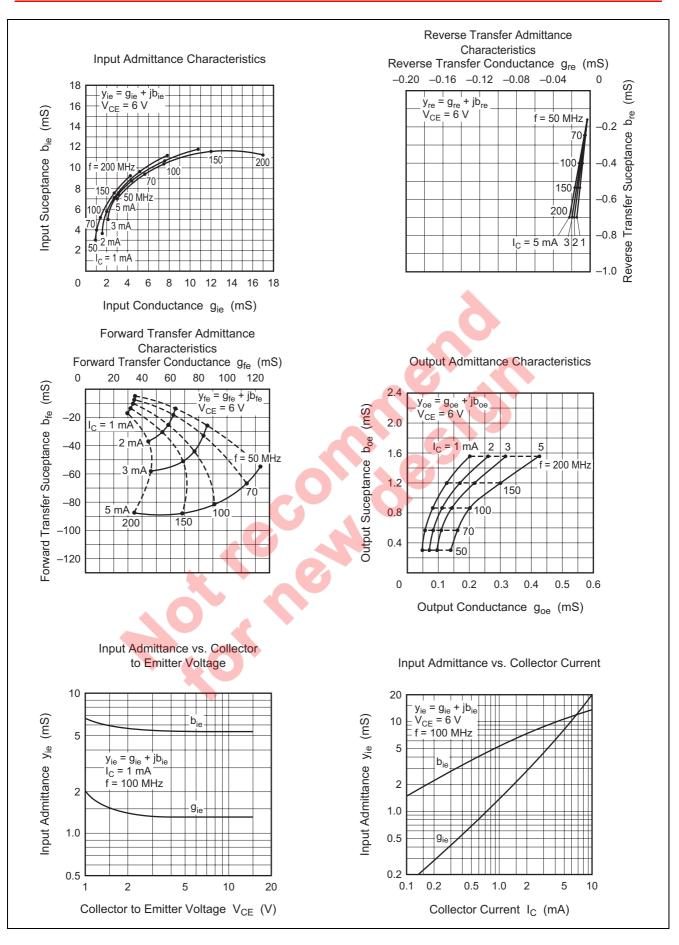


## **Main Characteristics**

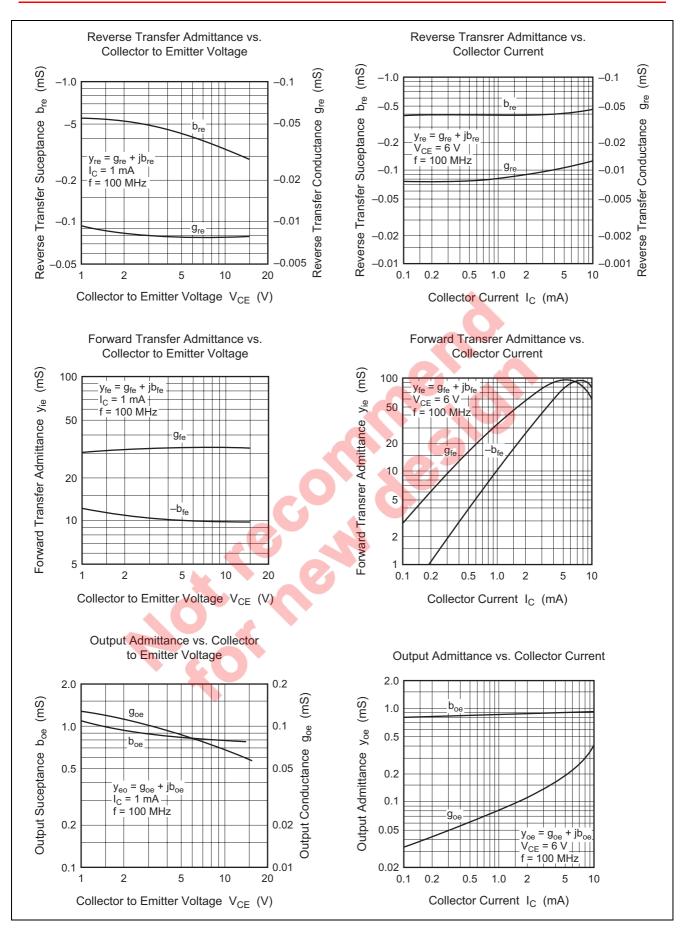






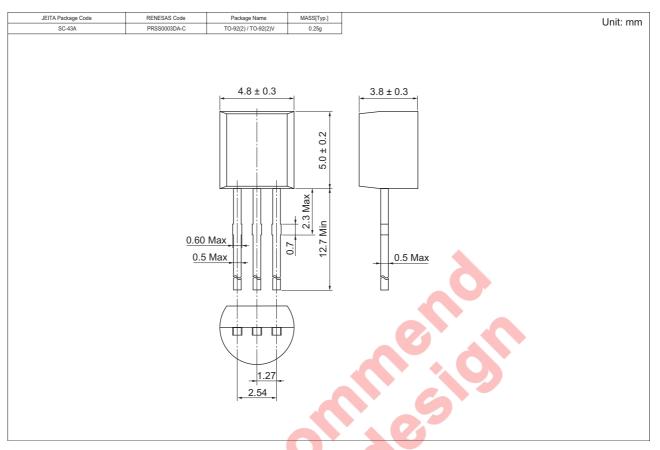








## Package Dimensions



## **Ordering Information**

Part Name	Quan	tity	Shipping Container
2SC535BTZ	2500	Ho	ld Box, Radial Taping
2SC535CTZ			

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



## Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Keep safety first in your circuit designs! 1. Renesas Technology Corp. puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

### Notes regarding these materials

- Notes regarding these materials
  1. These materials are intended as a reference to assist our customers in the selection of the Renesas Technology Corp. product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Renesas Technology Corp. or a third party.
  2. Renesas Technology Corp. assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.
  3. All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Renesas Technology Corp. virbutout notice due to product improvements or other reasons. It is therefore recommended that customers contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor for the latest product information before purchasing a product listed herein.
  The information described here may contain technical inaccuracies or typographical errors. Renesas Technology Corp. assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors. Please also pay attention to information published by Renesas Technology Corp. by various means, including the Renesas Technology Corp. Semiconductor home page (http://www.renesas.com).
  4. When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to

- Nome page (ntp://www.renesas.com).
  4. When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Renesas Technology Corp. assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.
  5. Renesas Technology Corp. semiconductors are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.
- use. 6. The prior written approval of Renesas Technology Corp. is necessary to reprint or reproduce in whole or in part these materials. 7. If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination. Any diversion or reexport contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited. 8. Please contact Renesas Technology Corp. for further details on these materials or the products contained therein.



### **RENESAS SALES OFFICES**

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

http://www.renesas.com

Renesas Technology America, Inc. 450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K. Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology Hong Kong Ltd. 7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd. Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

### Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

### Renesas Technology Malaysia Sdn. Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510